C4D02120E

Silicon Carbide Schottky Diode

Z-Rec® Rectifier

V_{RRM}	=	1200 V
I_F (T_C=135°C)	=	4.5 A
Q_c	=	11 nC

Features

- 1.2kV Schottky Rectifier
- Optimized for PFC Boost Diode Application
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Positive Temperature Coefficient on V_F

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

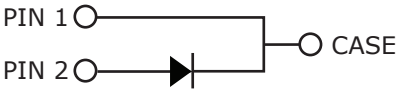
- Solar Inverters
- Power Factor Correction
- LED Lighting Power Supplies
- X-Ray Tube Power Drivers
- EV Charging and Power Conversion

Package

TO-252-2

Halogen-Free

RoHS



Part Number	Package	Marking
C4D02120E	TO-252-2	C4D02120

Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V_{RSM}	Surge Peak Reverse Voltage	1300	V		
V_{DC}	DC Blocking Voltage	1200	V		
I_F	Maximum DC Current	9 4.5 2	A	T_C=25°C T_C=135°C T_C=162°C	
I_{FRM}	Repetitive Peak Forward Surge Current	14.4 10	A	T_C=25°C, t_P=10 ms, Half Sine pulse T_C=110°C, t_P=10 ms, Half Sine pulse	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	19 16.5	A	T_C=25°C, t_P=10 ms, Half Sine pulse T_C=110°C, t_P=10 ms, Half Sine pulse	
$I_{F,Max}$	Non-Repetitive Peak Forward Current	200 160	A	T_C=25°C, t_P=10 µs, Pulse T_C=110°C, t_P=10 µs, Pulse	
P_{tot}	Power Dissipation	51.7 22.4	W	T_C=25°C T_C=110°C	
T_J	Operating Junction Range	-55 to +175	°C		
T_{stg}	Storage Temperature Range	-55 to +135	°C		

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.4 1.9	1.8 3	V	I_F = 2 A T_J=25°C I_F = 2 A T_J=175°C	
I_R	Reverse Current	10 40	50 150	μA	V_R = 1200 V T_J=25°C V_R = 1200 V T_J=175°C	
Q_C	Total Capacitive Charge	11		nC	V_R = 800 V, I_F = 2A d*i*/d*t* = 200 A/μs T_J = 25°C	
C	Total Capacitance	167 11 8		pF	V_R = 0 V, T_J = 25°C, f = 1 MHz V_R = 400 V, T_J = 25°C, f = 1 MHz V_R = 800 V, T_J = 25°C, f = 1 MHz	
E_C	Capacitance Stored Energy	3.2		μJ	V_R = 800 V	Fig. 7

Note:
1. This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit
$R_{\theta JC}$	TO-252 Package Thermal Resistance from Junction to Case	2.9	°C/W

Typical Performance

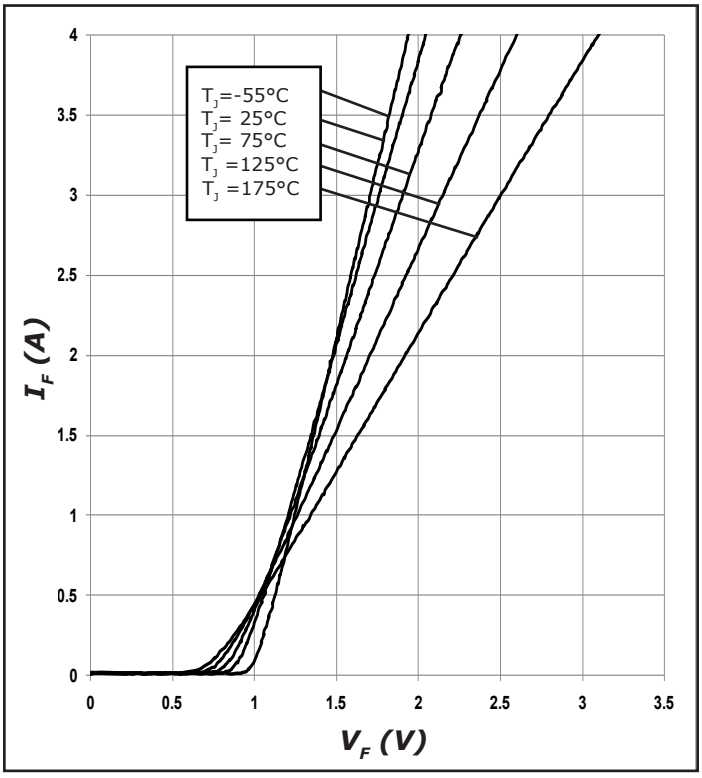


Figure 1. Forward Characteristics

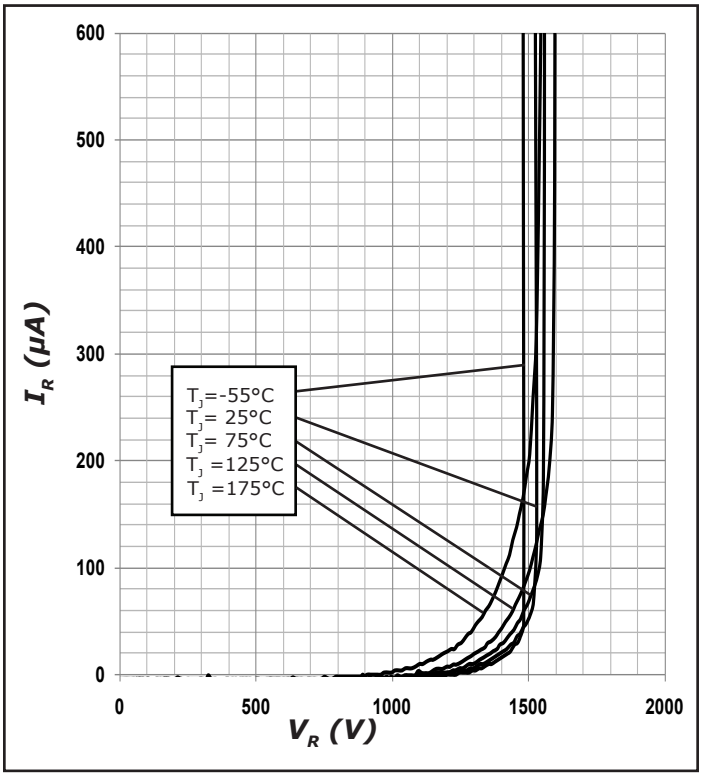


Figure 2. Reverse Characteristics

Typical Performance

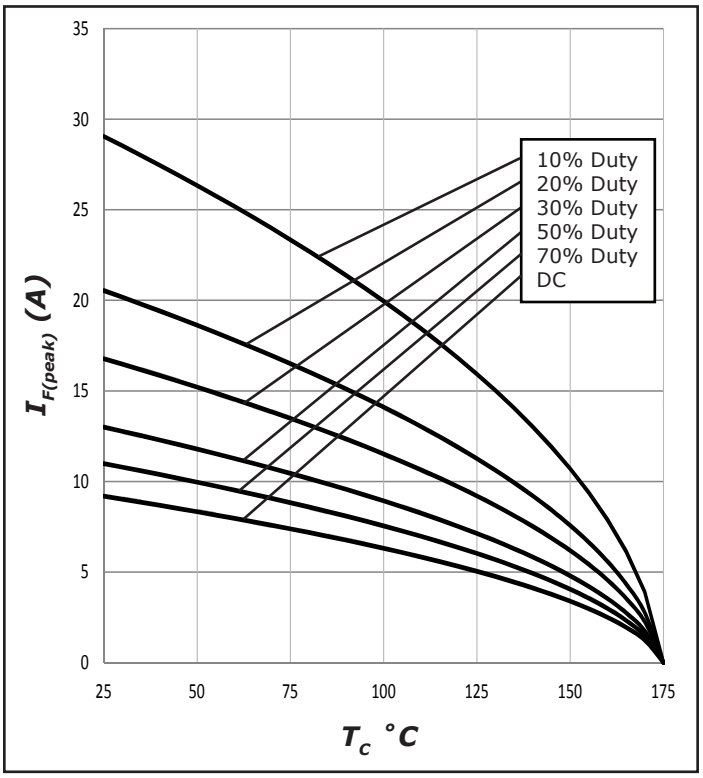


Figure 3. Current Derating

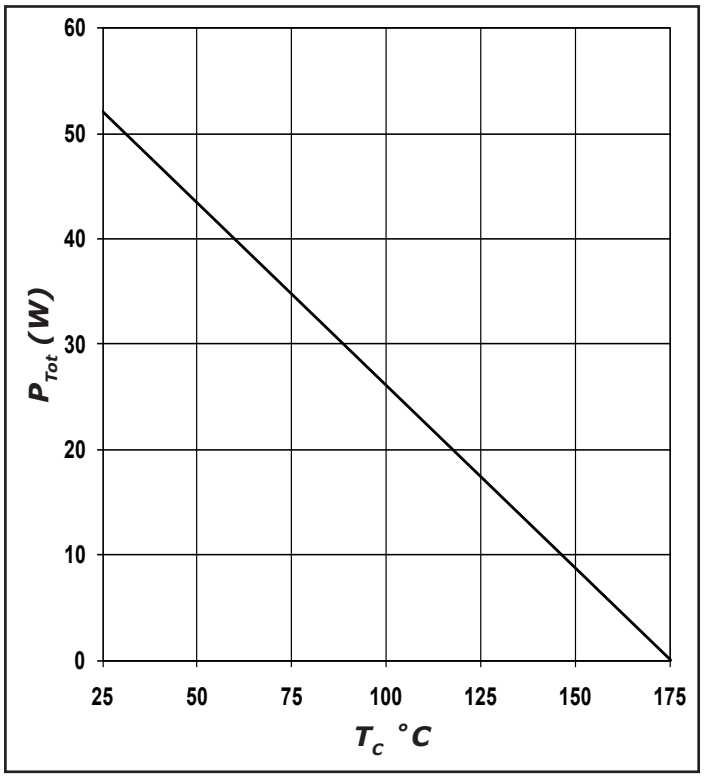


Figure 4. Power Derating

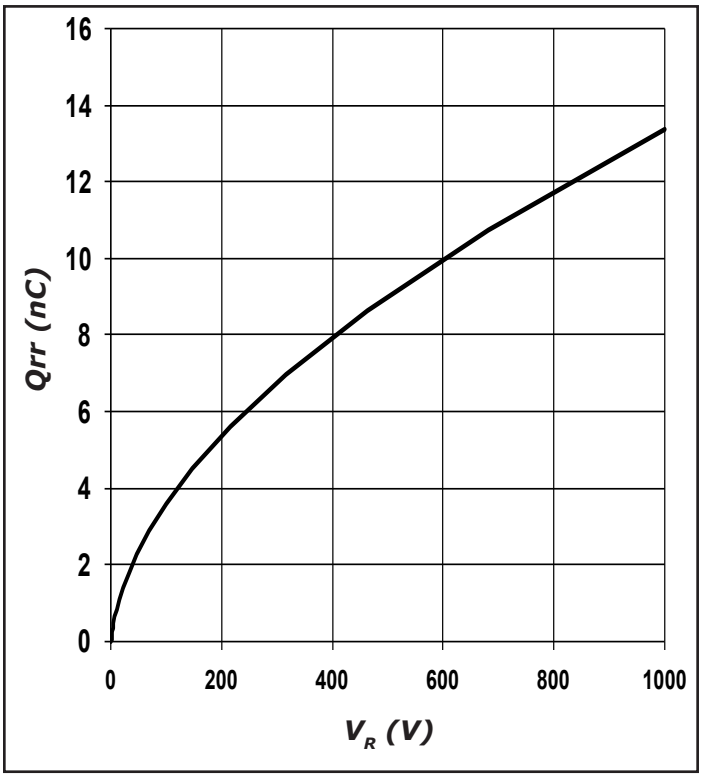


Figure 5. Recovery Charge vs. Reverse Voltage

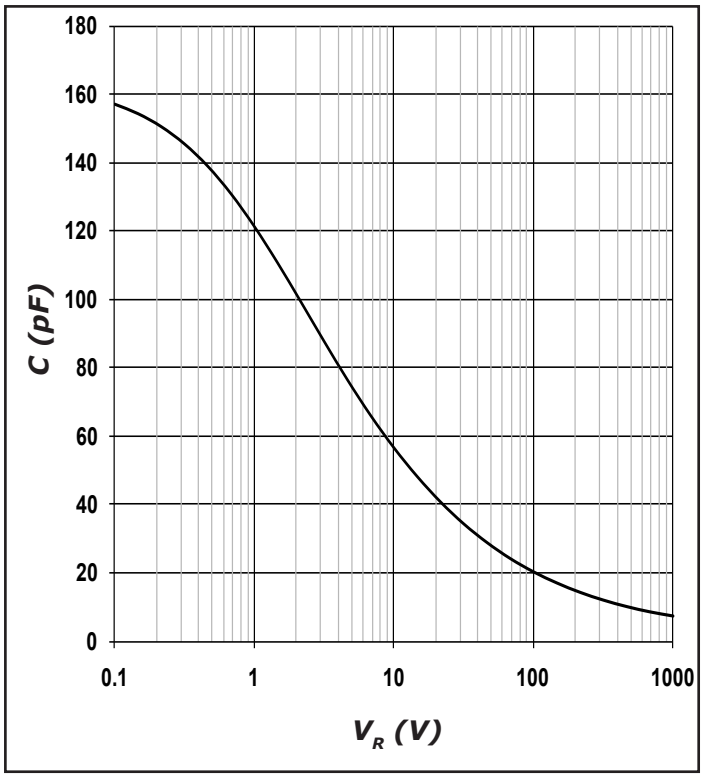


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance

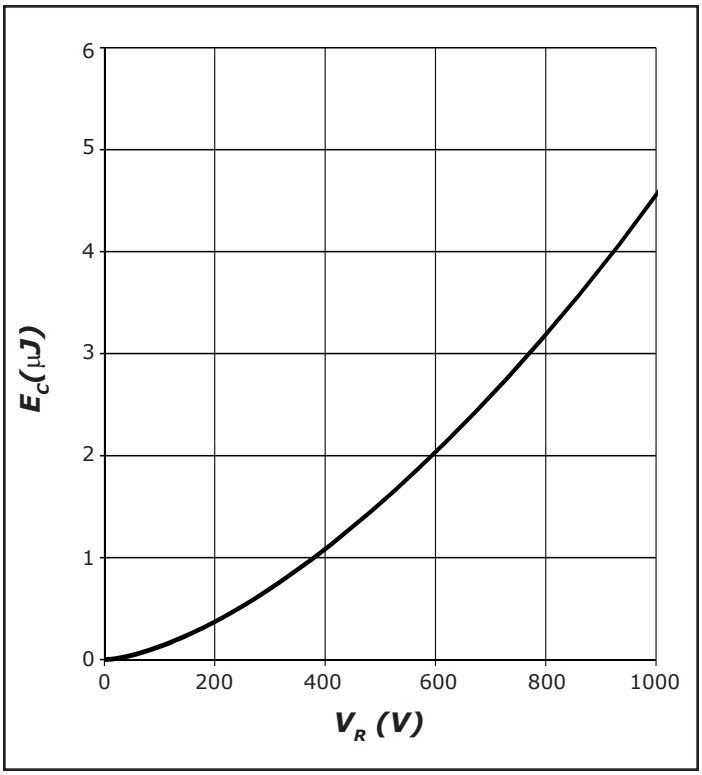


Figure 7. Typical Capacitance Stored Energy

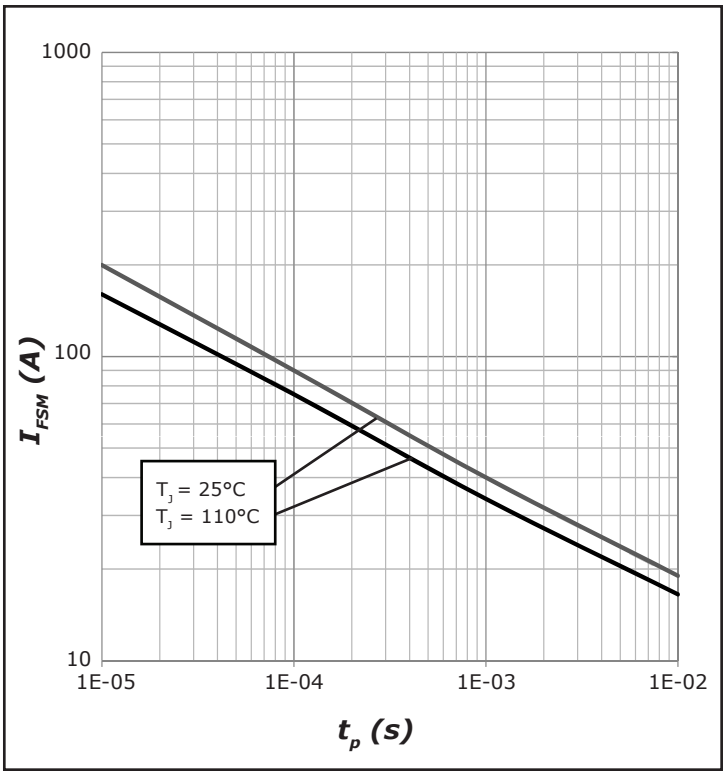


Figure 8. Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

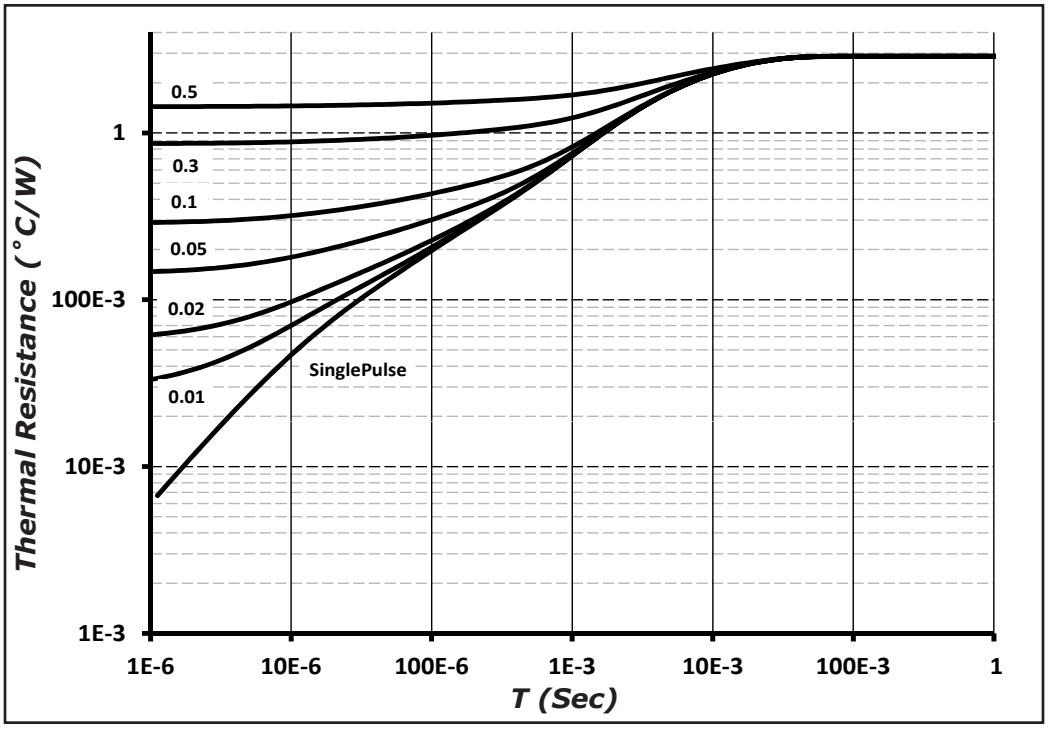
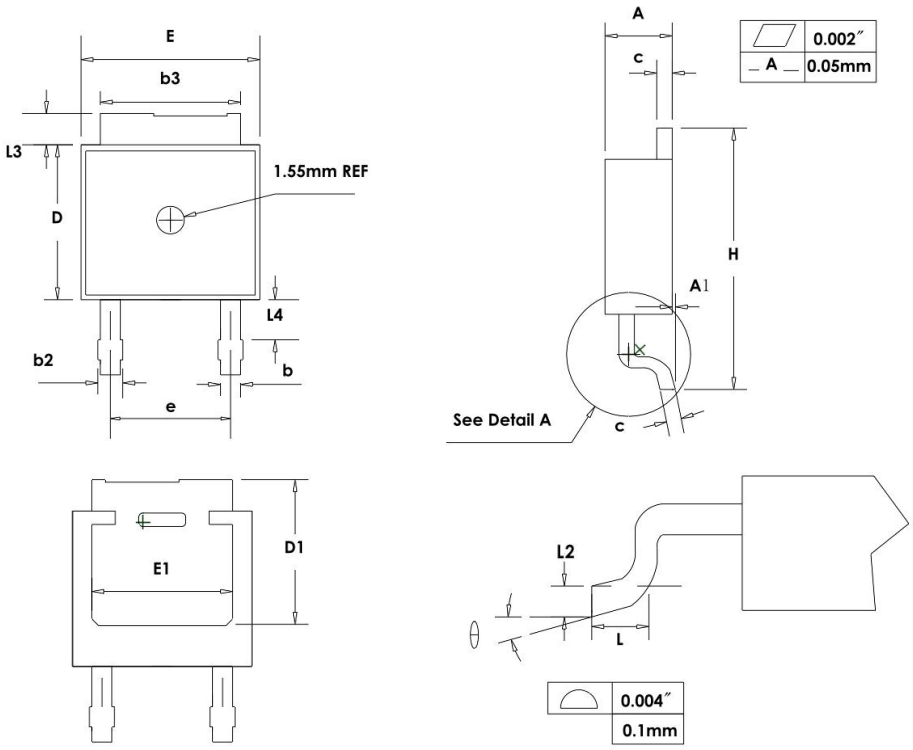


Figure 9. Transient Thermal Impedance

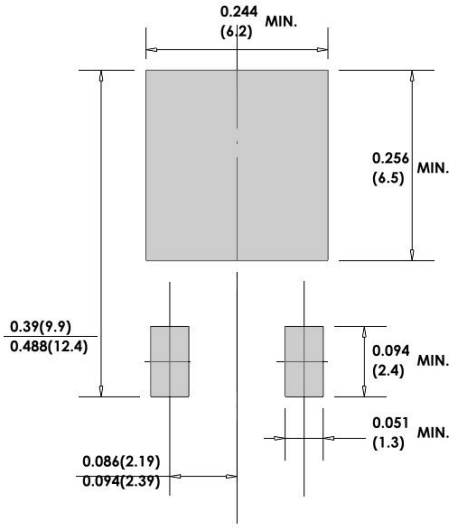
Package Dimensions

Package TO-252-2



SYMBOL	MILLIMETERS	
	MIN	MAX
A	2.19	2.38
A1	–	0.13
b	0.64	0.89
b2	0.84	1.14
b3	5.21	5.46
c	0.46	0.61
D	5.97	6.22
D1	5.21	—
E	6.35	6.73
E1	4.83	—
e	4.58BSC	
H	9.65	10.41
L	1.40	1.78
L2	0.51BSC	
L3	0.89	1.27
L4	0.64	1.01
θ	0	8

Recommended Solder Pad Layout

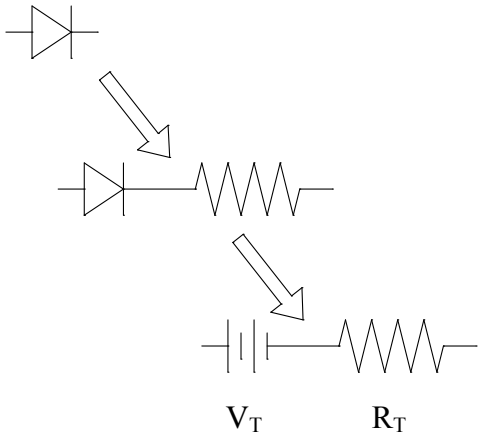


TO-252-2

Part Number	Package	Marking
C4D02120E	TO-252-2	C4D02120

Note: Recommended soldering profiles can be found in the applications note here:
http://www.cree.com/power_app_notes/soldering

Diode Model



$$V_{fT} = V_T + If * R_T$$

$$V_T = 0.9592 + (T_J * -1.20 * 10^{-3})$$
$$R_T = 0.1673 + (T_J * 2.10 * 10^{-3})$$

Note: T_J = Diode Junction Temperature in Degrees Celsius, valid from 25°C to 175°C

Notes

- **RoHS Compliance**
  The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Cree representative or from the Product Documentation sections of www.cree.com.

- **REACh Compliance**
  REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future,please contact a Cree representative to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

- This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control systems.

Related Links

- Cree SiC Schottky diode portfolio: http://www.cree.com/diodes
- C3D Spice models: http://response.cree.com/Request_Diode_model
- SiC MOSFET and diode reference designs: http://response.cree.com/SiC_RefDesigns

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
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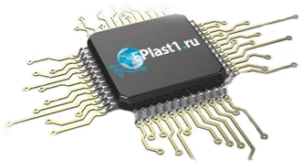

Как с нами связаться

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